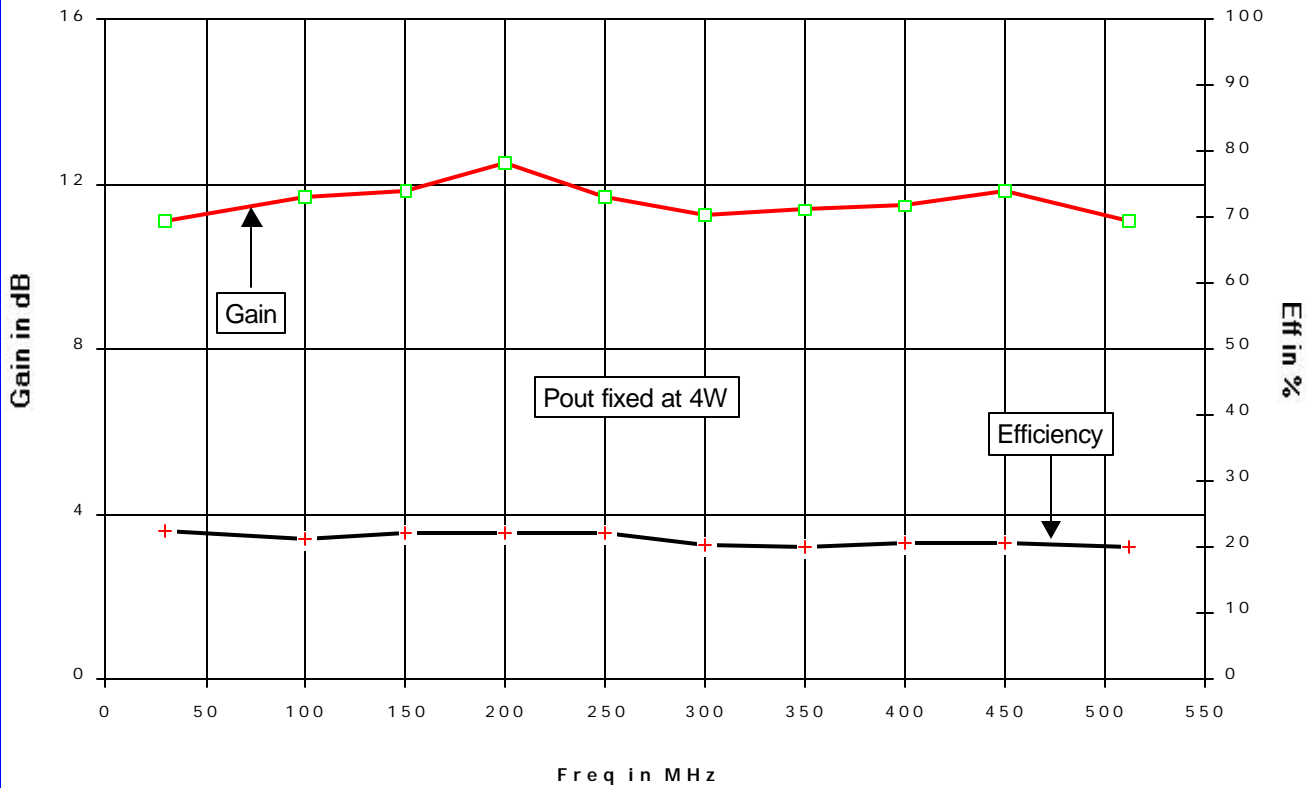
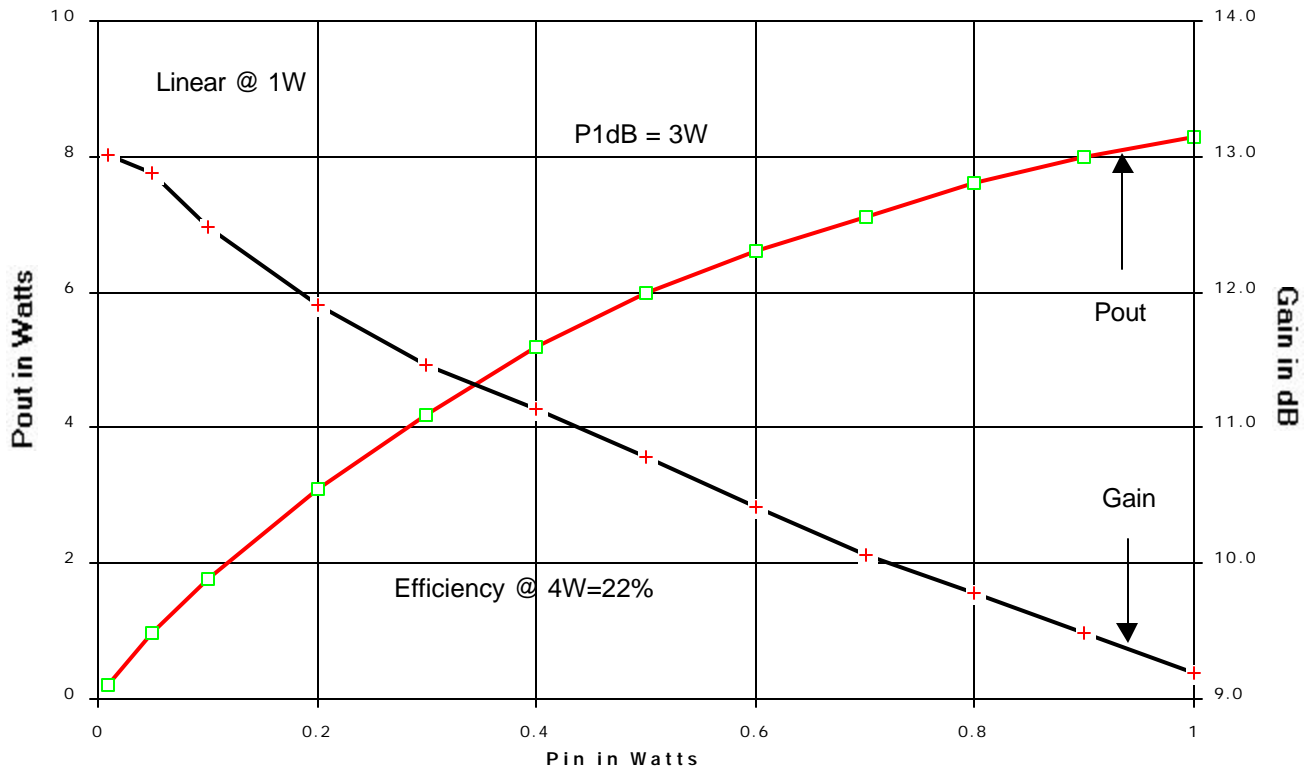


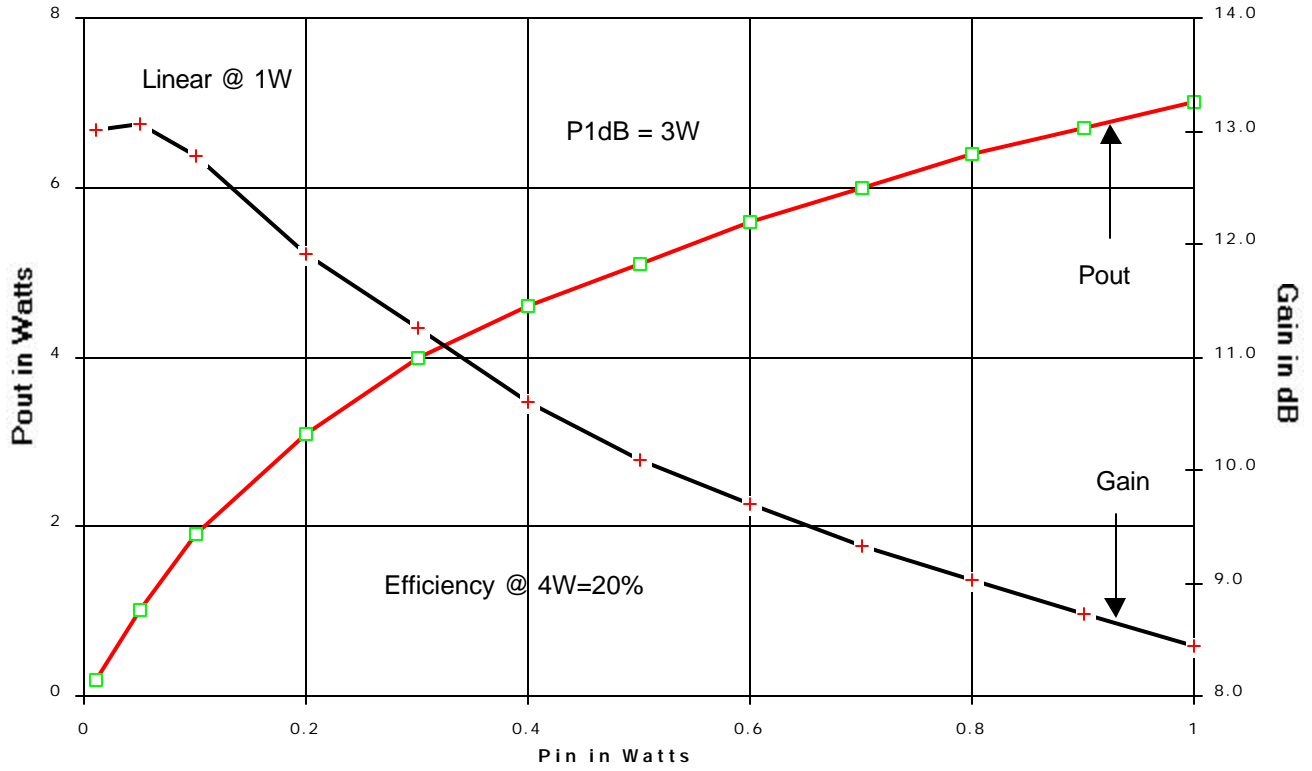
TB-163 SQ201 Gain/Efficiency vs Frequency; $V_{ds}=28V_{dc}$ $I_{dq}=.4A$



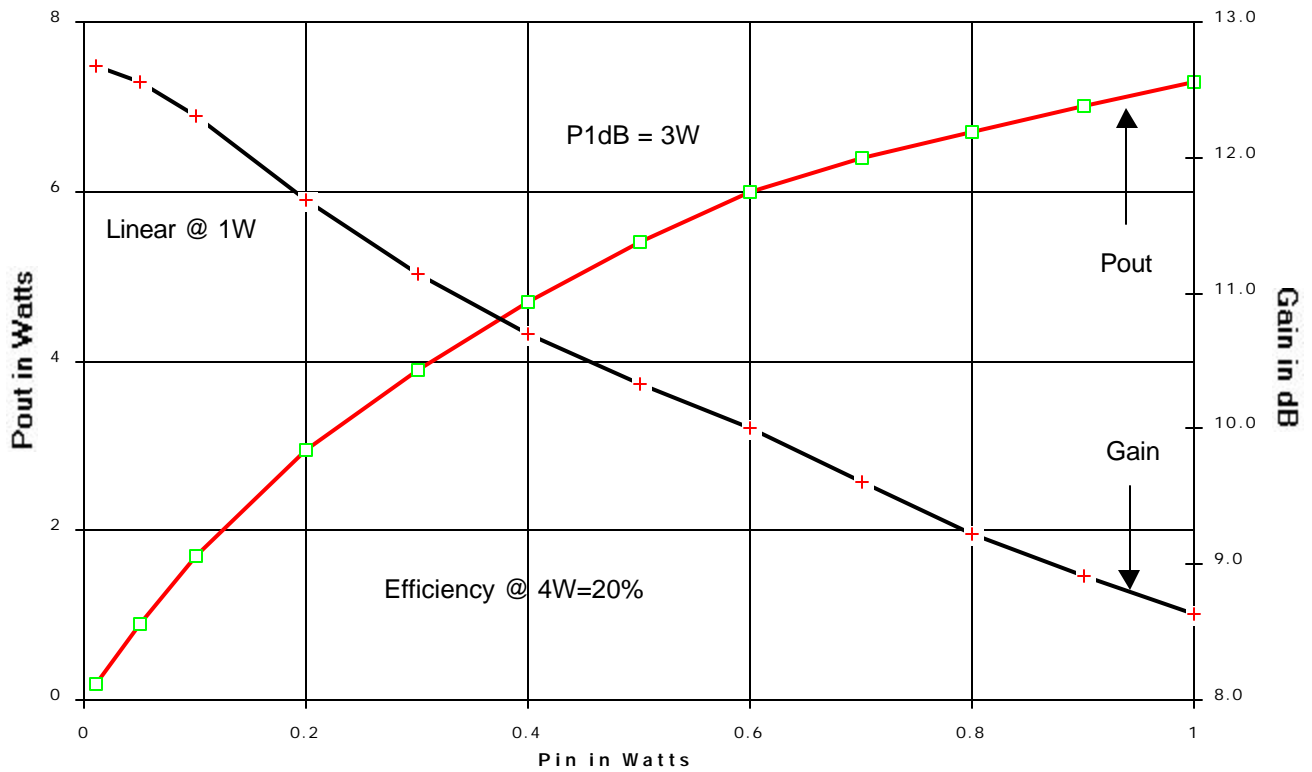
TB-163 SQ201 Pout vs Pin Freq=250MHz $V_{ds}=28V_{dc}$ $I_{dq}=400ma$



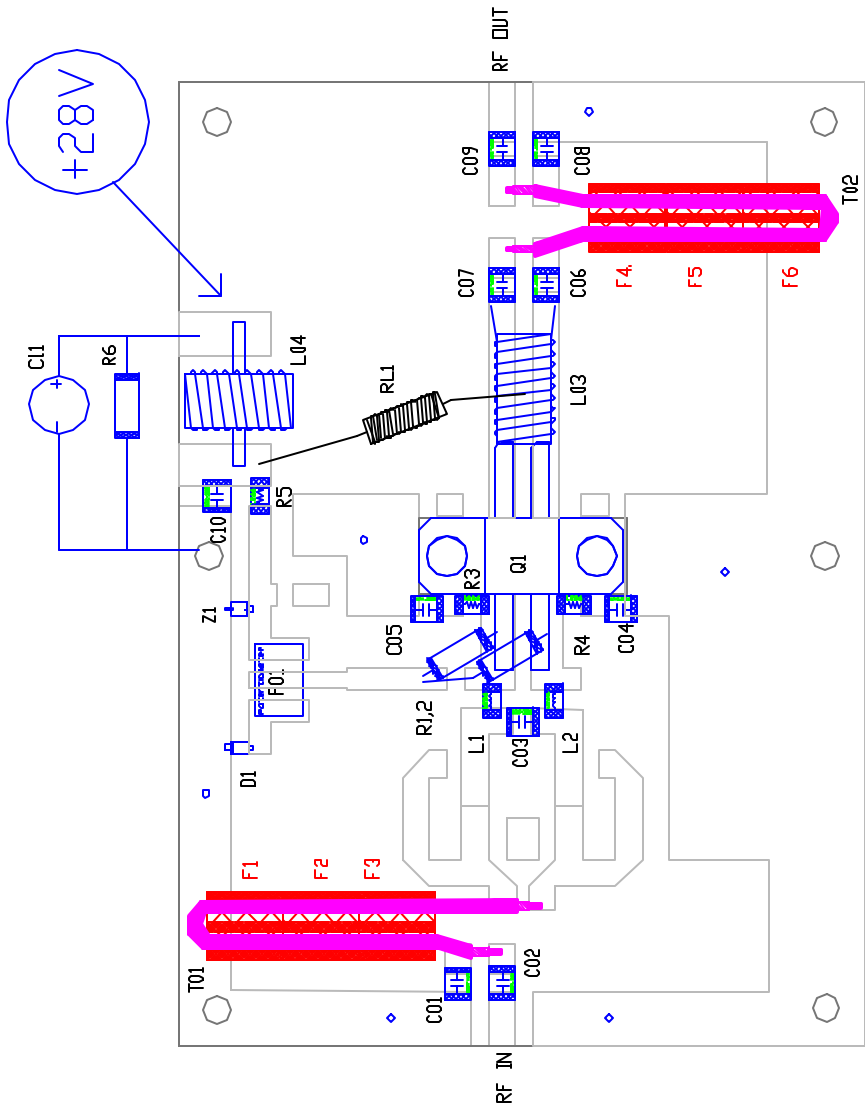
TB-163 SQ201 Pout vs Pin Freq=30MHz Vds=28Vdc Idq=400ma



TB-163 SQ201 Pout vs Pin Freq=512MHz Vds=28Vdc Idq=400ma



SYMBOL	VALUE	DESCRIPTION
C01,C06,07,09	1000pF	ATC100B CHIP CAP.
C02,C08	470pF	ATC100B CHIP CAP.
C03	7.5pF	ATC100B CHIP CAP.
C04,05,10	10nF	ATC100B CHIP CAP.
C11	47uF	ATC100B CHIP CAP.
R1,2	9.09k	1/4W axial resistor
R3,4	47ohm	0805 chip resistor
R5	3.9k	0805 chip resistor
P01	10k	multi-turn POT
RL1	22AWG	around 220ohm 1/2W
D1	---	general purpose
Z1	7.5V	5mA Zener diode
T01,T02	2500mil	UT34-50ohm Coaxial balun
L01,L02	22AWG	ID:0,08", 2turns
L03	22AWG	850mu,center-tap,18 turns
L04	22AWG	850mu, 10 turns
F1-6	125mu	Amidon BN-61-2402
Q1	SQ201	Polyfet Transistor
VDD	28V	DC Power Supply
Bias	400mA	Bias Current



DRN BY: Cunningham/3/15/02
CHKD :
ELECT : J Citrolo
MECH : J Citrolo
PRDC :
QUAL :
PGMS :

POLYFET RF DEVICES	
30--512MHZ Amplifier	
SIZE	FSCM NO
TB163	LAYOUT
REV	0
SCALE :	1 : 1
SHEET	1 OF 1

PCB Material : Double Side FR4
ER=3.55, H=0.032", T=0.001"

